July 2000

FDD6612A

FDD6612A N-Channel, Logic Level, PowerTrench[™] MOSFET

General Description

This N-Channel Logic level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

Applications

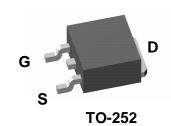
- DC/DC converter
- Motor drives

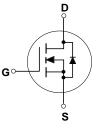
Features

• 30 A, 30 V.
$$R_{DS(on)} = 0.020 \ \Omega \ @ V_{GS} = 10 V$$

 $R_{DS(on)} = 0.028 \ \Omega \ @ V_{GS} = 4.5 V.$

- Low gate charge (9nC typical).
- Fast switching speed.
- High performance trench technology for extremely low R_{DS(on)}.





Absolute Maximum Ratings TA=25°C unless otherwise noted

| Symbol | Parameter | | Ratings | Units | |
|-----------------------------------|--|-----------|-------------|-------|--|
| V _{DSS} | Drain-Source Voltage | | 30 | V | |
| V _{GSS} | Gate-Source Voltage | | ±20 | V | |
| ID | Drain Current - Continuous | (Note 1) | 30 | A | |
| | | (Note 1a) | 9.5 | | |
| | Drain Current - Pulsed | | 60 | | |
| PD | Maximum Power Dissipation @ $T_c = 25^{\circ}C$ | (Note 1) | 36 | W | |
| | $T_A = 25^{\circ}C$ | (Note 1a) | 2.8 | | |
| | $T_A = 25^{\circ}C$ | (Note 1b) | 1.3 | | |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | | -55 to +150 | °C | |

Thermal Characteristics

| R _{θJC} | Thermal Resistance, Junction-to- Case | (Note 1) | 3.5 | °C/W |
|------------------|--|-----------|-----|------|
| $R_{\theta J A}$ | Thermal Resistance, Junction-to- Ambient | (Note 1b) | 96 | °C/W |

Package Marking and Ordering Information

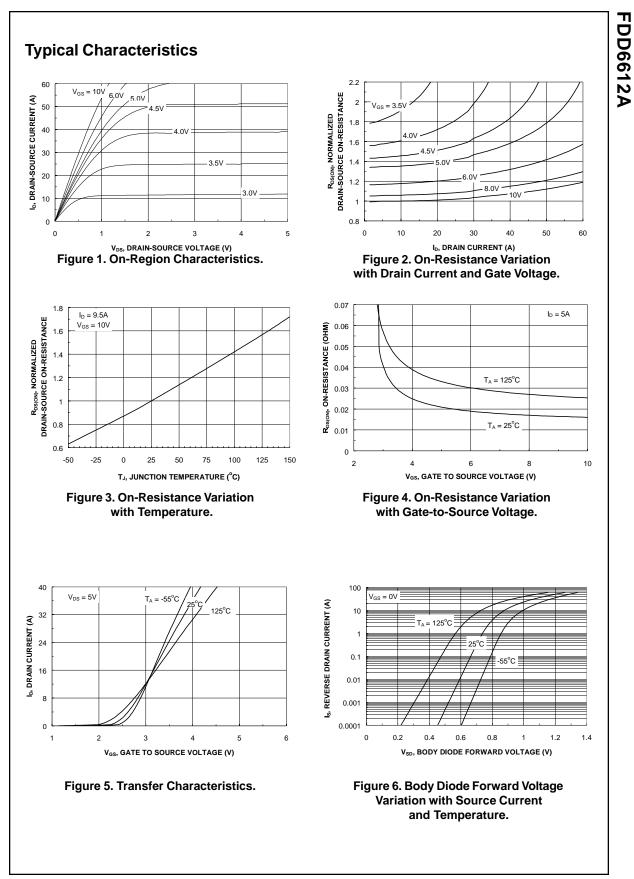
| Device Marking | Device | Reel Size | Tape width | Quantity |
|----------------|----------|-----------|------------|----------|
| FDD6612A | FDD6612A | 13" | 16mm | 2500 |

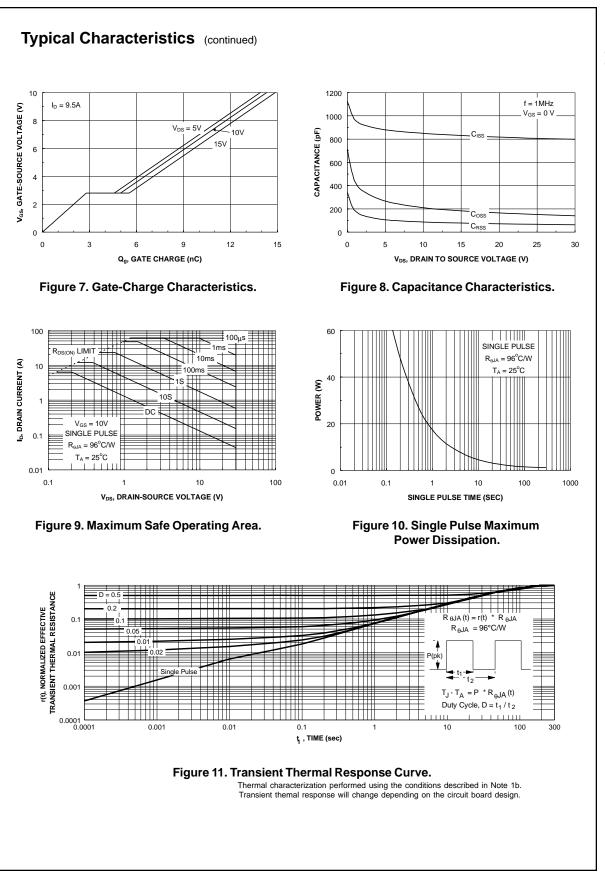
| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|-------------------------------|---|--|-----------------------------------|---|-------------------------|-------|
| Off Char | acteristics | | | | | • |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 V, I_{D} = 250 \mu A$ | 30 | | | V |
| <u>∆</u> BV⊡ss ∆Tj | Breakdown Voltage Temperature Coefficient | $I_D = 250_{Ll}A$, Referenced to $25^{\circ}C$ | | 22 | | mV/∘C |
| DSS | Zero Gate Voltage Drain Current | $V_{DS} = 24 V, V_{GS} = 0 V$ | | | 1 | μA |
| GSSF | Gate-Body Leakage Current, Forward | $V_{GS} = 20V, V_{DS} = 0 V$ | | | 100 | nA |
| GSSR | Gate-Body Leakage Current, Reverse | $V_{GS} = -20 V, V_{DS} = 0 V$ | | | -100 | nA |
| On Chara | acteristics (Note 2) | | | | | |
| / _{GS(th)} | Gate Threshold Voltage | $V_{\text{DS}} = V_{\text{GS}}, \ I_{\text{D}} = 250 \ \mu\text{A}$ | 1 | 1.6 | 3 | V |
| _VGS(th) ∧T」 | Gate Threshold Voltage Temperature Coefficient | $I_D = 250_{LI}A$, Referenced to $25^{\circ}C$ | | -4.2 | | mV/∘C |
| ₹ _{DS(on)} | Static Drain-Source On-Resistance | $V_{GS} = 10 \text{ V}, I_D = 9.5 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 9.5\text{ A}, T_J = 125 \circ \text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 8 \text{ A}$ | | 0.017 0.026 0.024 | 0.020 0.036 0.028 | Ω |
| D(on) | On-State Drain Current | V_{GS} =10 V, V_{DS} = 5 V | 40 | | | А |
| FS | Forward Transconductance | V_{DS} =5 V, I_D = 9.5 A | | 22 | | S |
| Dvnamic | Characteristics | | | | | |
| iss | Input Capacitance | $V_{DS} = 15 V, V_{GS} = 0 V,$ | | 830 | | pF |
| Soss | Output Capacitance | f = 1.0 MHz | | 185 | | pF |
| Prss | Reverse Transfer Capacitance | - | | 80 | | pF |
| Switchin | g Characteristics (Note 2) | | | | | |
| d(on) | Turn-On Delay Time | $V_{DD} = 15 \text{ V}, \text{ I}_{D} = 1 \text{ A},$ | | 6 | 12 | ns |
| r | Turn-On Rise Time | V_{GS} = 10 V, R_{GEN} = 6 Ω | | 10 | 18 | ns |
| d(off) | Turn-Off Delay Time | 1 | | 18 | 29 | ns |
| f | Turn-Off Fall Time | | | 5 | 12 | ns |
| $\mathfrak{Z}_{\mathfrak{q}}$ | Total Gate Charge | $V_{DS} = 15 \text{ V}, \text{ I}_{D} = 9.5 \text{ A},$ | | 9 | 13 | nC |
| ⊋ _{gs} | Gate-Source Charge | $V_{GS} = 5 V,$ | | 2.8 | | nC |
| 2 _{gd} | Gate-Drain Charge | | | 3.1 | | nC |
| Drain-So | urce Diode Characteristics | and Maximum Ratings | | | | |
| S | Maximum Continuous Drain-Source | e Diode Forward Current | | | 2.3 | А |
| / _{SD} | Drain-Source Diode ForwardVoltage | $V_{GS} = 0 \ V, \ I_S = 2.3 \ A$ (Note 2) | | 0.80 | 1.2 | V |
| 0071 | a of the junction-to-case and case-to-ambient re teed by design while R _{6JA} is determined by the a) R _{6JA} = 45 ^o C/W when on a 1in ² pad of 2oz co | user's board design. mounted b) R _{θJ} | _А = 96 ⁰ СЛ | d as the dr. N when mo of 2oz cop | unted | |

2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

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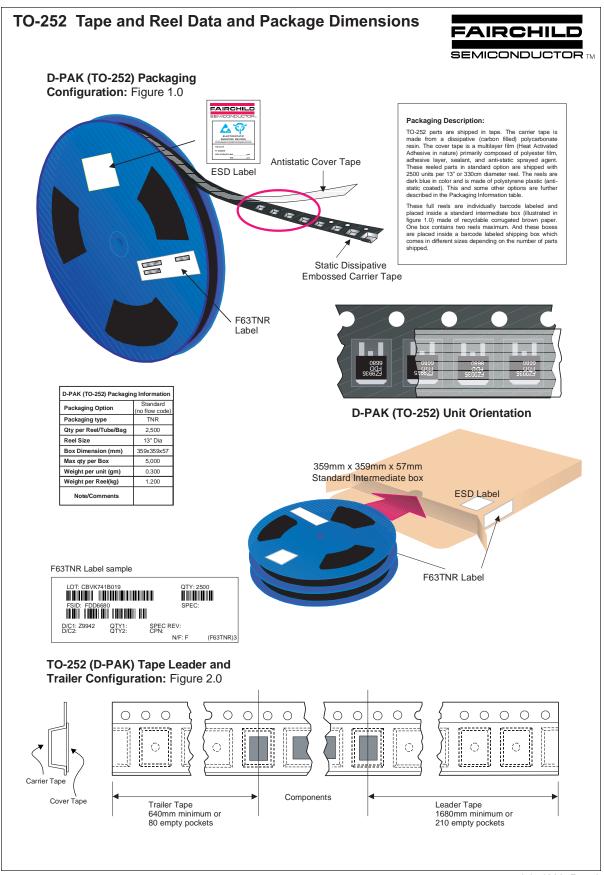
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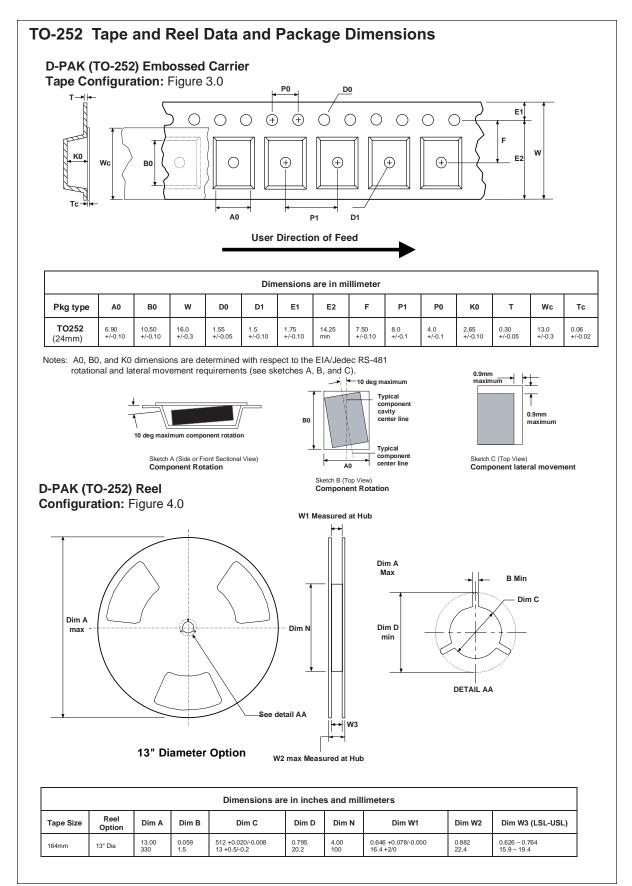


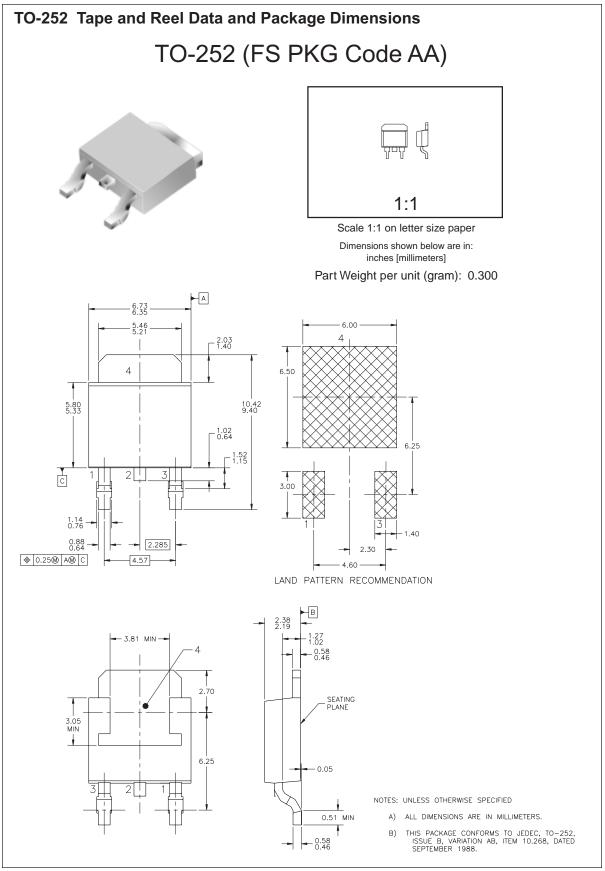
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PRODUCT STATUS DEFINITIONS

Definition of Terms

| Datasheet Identification | Product Status | Definition |
|--------------------------|---------------------------|---|
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